

N-CHANNEL SILICON POWER MOSFET

FUJI
ELECTRIC

FUJI POWER MOSFET Super FAP-G Series

■ Features

High speed switching	Low on-resistance
No secondary breakdown	Low driving power
Avalanche-proof	

■ Applications

Switching regulators DC-DC converters
UPS (Uninterruptible Power Supply)

■ Maximum ratings and characteristic

● Absolute maximum ratings
(Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit	Remarks
Drain-source voltage	V _{DS}	500	V	V _{GS} =-30V
	V _{DSX}	500	V	
Continuous Drain Current	I _D	11	A	
Pulsed Drain Current	I _{D(puls)}	±44	A	
Gate-Source Voltage	V _{GS}	±30	V	
Maximum Avalanche current	I _{AR}	11	A	Note *1
Non-Repetitive Maximum Avalanche Energy	E _{AS}	453.9	mJ	Note *2
Repetitive Maximum Avalanche Energy	E _{AR}	6.0	mJ	Note *3
Maximum Drain-Source dV/dt	dV _{DS} /dt	20	kV/μs	V _{DS} ≤500V
Peak Diode Recovery dV/dt	dV/dt	5	kV/μs	Note *4
Max. Power Dissipation	P _D	60	W	T _c =25°C
		2.16		T _a =25°C
Operating and Storage Temperature range	T _{ch}	+150	°C	
	T _{stg}	-55 to +150	°C	
Isolation Voltage	V _{ISO}	2	kV _{rms}	t=60sec, f=60Hz

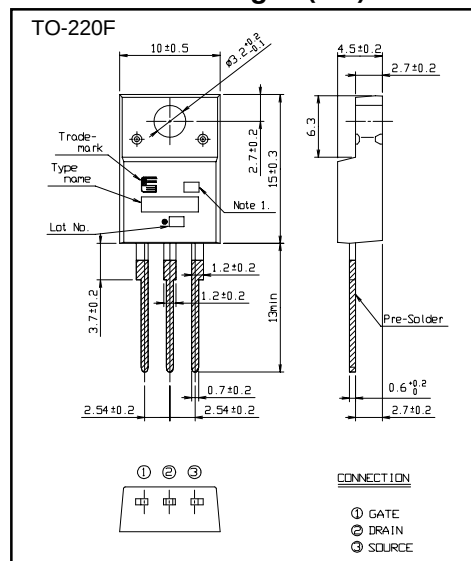
● Electrical characteristics (T_c =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA V _{GS} =0V	500			V
Gate Threshold Voltage	V _{GS(th)}	I _D = 250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =500V V _{GS} =0V			25	μA
		V _{DS} =400V V _{GS} =0V			250	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V V _{DS} =0V		10	100	nA
Drain-Source On-State Resistance	R _{DS(on)}	I _D =5.5A V _{GS} =10V		0.57	0.70	Ω
Forward Transconductance	g _{fs}	I _D =5.5A V _{DS} =25V	4.5	9.0		S
Input Capacitance	C _{iss}	V _{DS} =25V		950	1425	pF
Output Capacitance	C _{oss}	V _{GS} =0V		130	195	
Reverse Transfer Capacitance	C _{rss}	f=1MH		6.0	9.0	
Turn-On Time t _{on}	t _{d(on)}	V _{CC} =300V I _D =5.5A		16	24	ns
	t _r	V _{GS} =10V		6.0	9.0	
Turn-Off Time t _{off}	t _{d(off)}	R _{GS} =10 Ω		33	50	
	t _f			5.5	8.3	
Total Gate Charge	Q _G	V _{CC} =250V		25	38	nC
Gate-Source Charge	Q _{GS}	I _D =11A		10	15	
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		8.0	12	
Diode forward on-voltage	V _{SD}	I _F =11A V _{GS} =0V T _{ch} =25°C		1.10	1.50	V
Reverse recovery time	t _{rr}	I _F =11A V _{GS} =0V		650		ns
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		5.5		μC

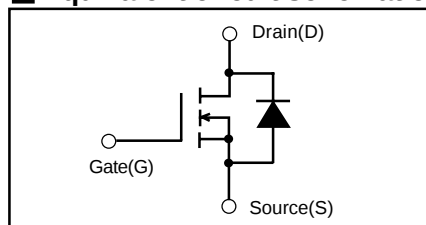
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			2.083	°C/W
	R _{th(ch-a)}	channel to ambient			58	°C/W

■ **Outline Drawings** (mm) 200406



■ Equivalent circuit schematic



—Note *1: $T_{ch} \leq 150^{\circ}\text{C}$, Repetitive and Non-repetitive

Note *2: Starting T_{ch}=25°C, I_{AS}=4.4A, L=43mH,

 $V_{CC}=50V, R_G=50\Omega$

EAS limited by maximum channel temperature and avalanche current.

See to the 'Avalanche Energy' graph

—Note *3:Repetitive rating:Pulse width limited by maximum channel temperature.

See to the 'Transient Thermal impedance' graph

Note *4: $I_F \leq -I_D$, $-di/dt = 50A/\mu s$, $V_{CC} \leq BV_{DSS}$, $T_{ch} \leq 150^\circ C$

Characteristics

